



Final

June 1996

ILC5061

SOT-23 Power Supply Reset Monitor

General Description

All-CMOS Monitor circuits in a 3-lead SOT-23 package offer the best performance in power consumption and accuracy.

The ILC5061 comes in a series of $\pm 1\%$ accurate trip voltages to fit most microprocessor applications. Even though its output can sink 2mA, the device draws only $1\mu\text{A}$ in normal operation.

Additionally, a built-in hysteresis of 5% of detect voltage simplifies system design.

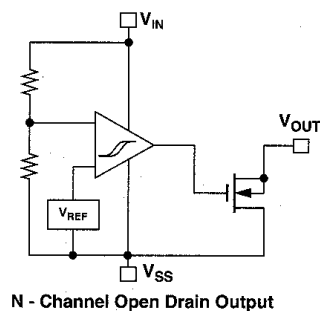
Features

- ◆ All-CMOS design in SOT-23 and SOT-89 package
- ◆ $\pm 1\%$ precision in Reset Detection
- ◆ Only $1\mu\text{A}$ of I_q
- ◆ 2mA of sink current capability
- ◆ Built-in hysteresis of 5% of detection voltage
- ◆ Voltage options of 2.6, 2.9, 3.1, 4.4, and 4.6V fit most supervisory applications

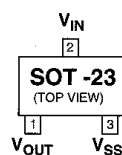
Applications

- ◆ Microprocessor reset circuits
- ◆ Memory battery back-up circuitry
- ◆ Power-on reset circuits
- ◆ Portable and battery powered electronics

Block Diagram



Pin-Package Configurations



Ordering Information*

ILC5061AM-26	2.6V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-29	2.9V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-31	3.1V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-44	4.4V $\pm 1\%$ Monitor in SOT-23
ILC5061AM-46	4.6V $\pm 1\%$ Monitor in SOT-23

* Standard product offering comes in tape & reel, quantity 3000 per reel, orientation right.

ILC5061 SOT-23 Power Supply Reset Monitor

Absolute Maximum Ratings ($T_A=25^\circ\text{C}$)

Parameter		Symbol	Ratings	Units
Input Voltage		V_{IN}	12	V
Output Current		I_{OUT}	50	mA
Output Voltage		V_{OUT}	$V_{SS}-0.3 \sim V_{IN}+0.3$	V
Continuous Total Power Dissipation	SOT-23	P_d	150	mW
Operating Ambient Temperature		T_{opr}	$-30 \sim +80$	$^\circ\text{C}$
Storage Temperature		T_{stg}	$-40 \sim +125$	$^\circ\text{C}$

Electrical Characteristics ILC5061 ($T_A=25^\circ\text{C}$)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Detect Fail Voltage	V_{DF}		$V_{DF} \times 0.99$	V_{DF}	$V_{DF} \times 1.01$	V
Hysteresis Range	V_{HYS}		$V_{DF} \times 0.02$	$V_{DF} \times 0.05$	$V_{DF} \times 0.08$	V
Supply Current	I_{SS}	$V_{IN}=1.5\text{V}$ $V_{IN}=2.0\text{V}$ $V_{IN}=3.0\text{V}$ $V_{IN}=4.0\text{V}$ $V_{IN}=5.0\text{V}$		0.9 1.0 1.3 1.6 2.0	2.6 3.0 3.4 3.8 4.2	μA
Operating Voltage	V_{IN}	$V_{DF}=2.1 \sim 6.0\text{V}$	1.5		10.0	V
Output Current	I_{OUT}	N-ch $V_{DS}=0.5\text{V}$ $V_{IN}=1.0\text{V}$ $V_{IN}=2.0\text{V}$ $V_{IN}=3.0\text{V}$ $V_{IN}=4.0\text{V}$ $V_{IN}=5.0\text{V}$		2.2 7.7 10.1 11.5 13.0		mA
Temperature Characteristics	$\Delta V_{DF}/(\Delta T_{opr} \cdot V_{DF})$	$-30^\circ\text{C} \leq T_{opr} \leq 80^\circ\text{C}$		± 100		ppm/ $^\circ\text{C}$
Delay Time (Release Voltage $\rightarrow$ Output Inversion)	t_{DLY} ($V_{DR} \rightarrow V_{OUT}$ Inversion)				0.2	ms

Note:

1. An additional resistor between the V_{IN} pin and supply voltage may cause deterioration of the characteristics due to increasing of V_{DR}

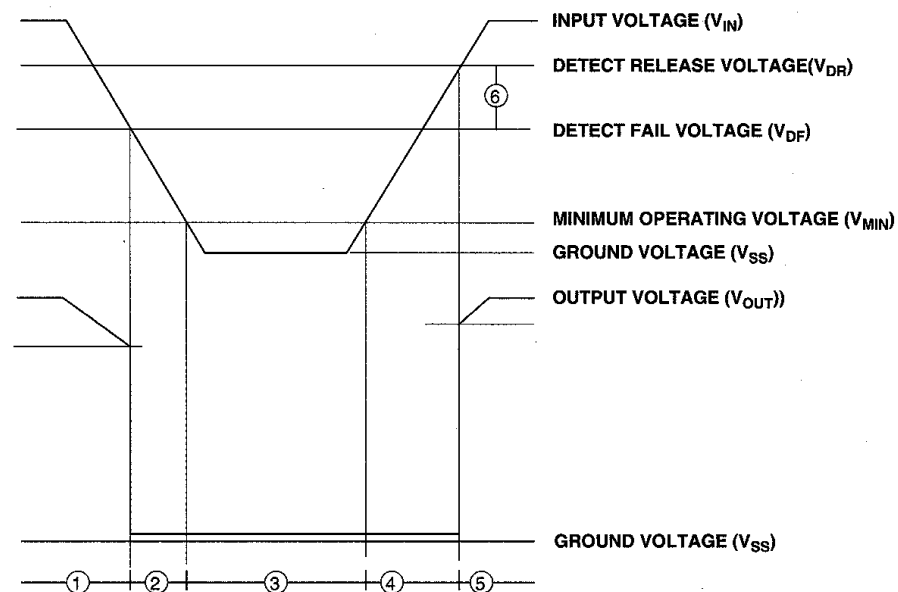
Functional Description

The following designators 1~6 refer to the timing diagram below.

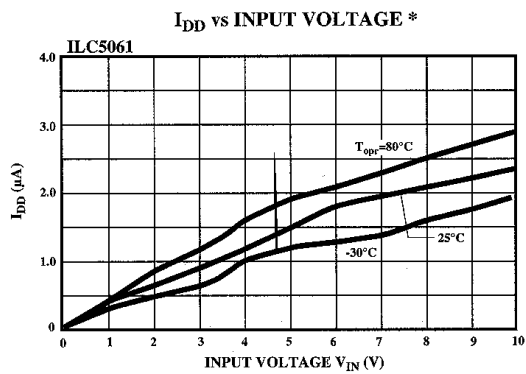
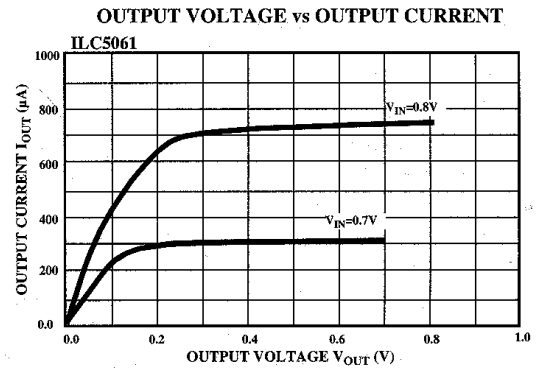
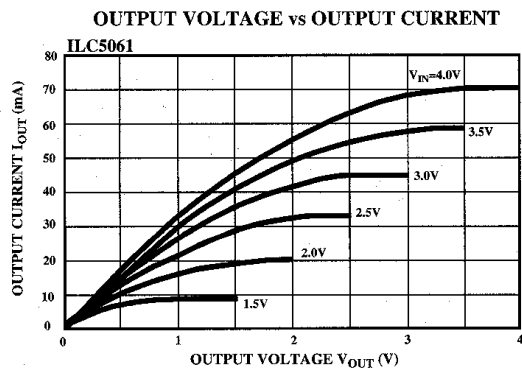
1. While the input voltage (V_{IN}) is higher than the detect voltage (V_{DF}); the V_{OUT} output pin is at high impedance state.
2. When the input V_{IN} voltage falls lower than V_{DF} , V_{OUT} drops near to ground voltage
3. If the input voltage further decreases below the minimum operating voltage (V_{MIN}), the V_{OUT} output becomes unstable. In this condition, if the V_{OUT} pin is pulled up, V_{OUT} indicates the V_{IN} voltage.

4. During an increase of the input voltage from the V_{SS} voltage, V_{OUT} is not stable in the voltage below the V_{MIN} . Exceeding that level, the output stays at the ground level (V_{SS}) between the minimum operating voltage (V_{MIN}) and detect release voltage (V_{DR}).
5. If the input voltage further increase more than V_{DR} ; the V_{OUT} output pin is at high impedance state.
6. The difference between V_{DR} and V_{DF} is the hysteresis in the system.

Timing Diagram



Typical Performance Characteristics General conditions for all curves.



* A spike of ½ to 1 μA may appear as V_{IN} crosses V_{DR} or V_{DF}

